TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

AC POWER CONTROL APPLICATIONS

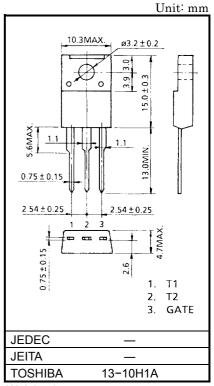
 $\begin{array}{ll} \bullet & \text{Repetitive Peak off-State Voltage} & : V_{DRM} = 400,\,600V \\ \bullet & \text{R.M.S On-State Current} & : I_{T \, (RMS)} = 12A \end{array}$

High Commutating (dv / dt)

• Isolation Voltage : $V_{Isol} = 1500V AC$

MAXIMUM RATINGS

CHARACTERI	STIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and	SM12GZ47 SM12GZ47A	V_{DRM}	400	V	
Repetitive Peak Reverse Voltage	SM12JZ47 SM12JZ47A	V DRM	600		
R. M. S. On-tate Currer (Full Sine Waveform TC	• •	I _{T (RMS)}	12	Α	
Peak One Cylce Surge On-State		Izou	120 (50Hz)	А	
Current (Non-Repetitive	e)	TSM	132 (60Hz)		
I ² t Limit Value		I ² t	72	A ² s	
Critical Rate of Rise of C Current	On-State (Note 1)	di / dt	50	A / μs	
Peak Gate Power Dissip	ation	P_{GM}	5	W	
Average Gate Power Dis	ssipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V_{FGM}	10	>	
Peak Gate Current		I_{GM}	2	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature R	ange	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V _{Isol}	1500	V	



Weight: 1.7g

Note 1: di / dt test condition $V_{DRM} = 0.5 \times Rated$ $I_{TM} \le 17A$ $t_{gw} \ge 10 \mu s$ $t_{gr} \le 250 ns$ $i_{gp} = I_{GT} \times 2.0$

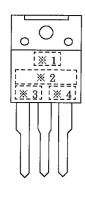
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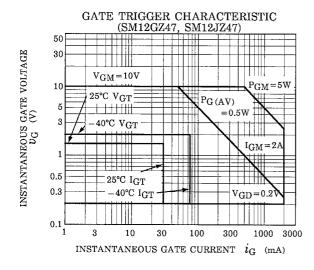
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

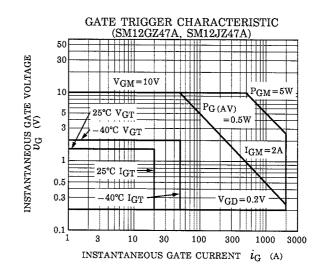
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Repetitive Peak	Off-Sta	te Current		I _{DRM}	V _{DRM} = Rated	_	_	20	μA	
Gate Trigger Voltage II III IV		I		V _D = 12V, R _L = 20Ω	T2 (+) , Gate (+)	-	_	1.5	V	
		П			T2 (+) , Gate (-)	_	_	1.5		
		III			T2 (-) , Gate (-)	-	_	1.5		
		IV			T2 (-) , Gate (+)	-	_	_		
						T2 (+) , Gate (+)	-	_	30	
	SM12	SM12GZ47 SM12JZ47	П			T2 (+) , Gate (-)	_	_	30	
	SM12		III			T2 (-) , Gate (-)	_	_	30	
Gate Trigger					V _D = 12V,	T2 (-) , Gate (+)	_	_	_	
Current		SM12GZ47A SM12JZ47A	I	I _{GT}	R _L = 20Ω	T2 (+) , Gate (+)	_	_	20	mA
	SM12		П			T2 (+) , Gate (-)	_	_	20	
	SM12		III			T2 (-) , Gate (-)	_	_	20	
						T2 (-) , Gate (+)	-	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 17A		_	_	1.5	V		
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		lн	V _D = 12V, I _{TM} = 1A			_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC			_	3.0	°C/W		
Critical Rate of		SM12GZ47 SM12JZ47		dv / dt	V _{DRM} = Rated, T _i = 125°C		_	300	_	- V/μs
Rise of Off-State Voltage	-	SM12GZ47 SM12JZ47		uv / ut	Exponential Rise		_	200	_	ν / μ5
Critical Rate of Rise of Off-State	9	SM12GZ47 SM12JZ47		(dv / dt) -	V _{DRM} = 400V, T _j = 125°C		10	_	_	V//110
Voltage at Commutation		SM12GZ47 SM12JZ47		(dv / dt) c	(di / dt) c = -6.5A / ms		4	_	_	- V/μs

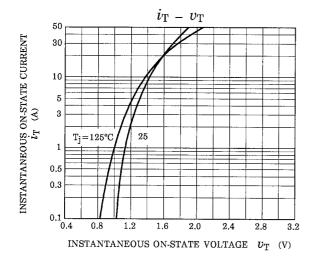
MARKING

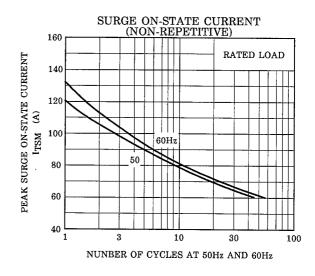


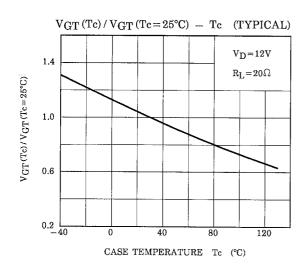
*NUMBE	ER		MARK		
*1		TOSHIBA PRODUCT MARK		7	
*2		SM12GZ47, SM12GZ47A	M12GZ47		
	TYPE	SM12JZ47, SM12JZ47A	M12JZ47		
*3			SM12GZ47A, SM12JZ47A	Α	
*4			(Starting from Alphabet A) (Last Decimal Digit of the Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998	

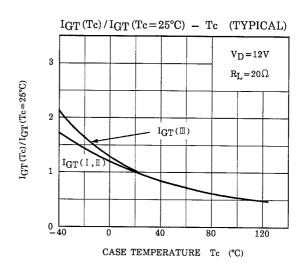


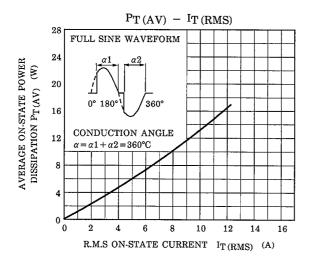


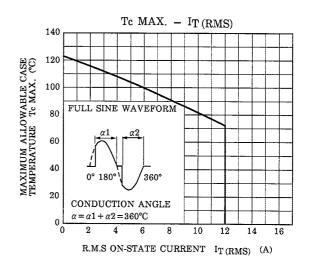


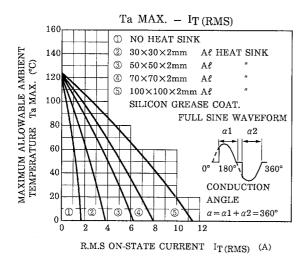


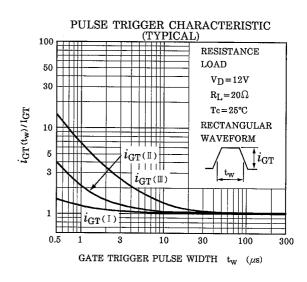


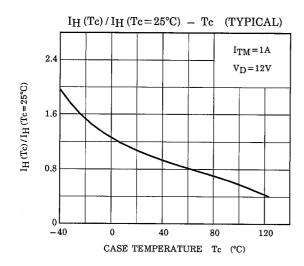


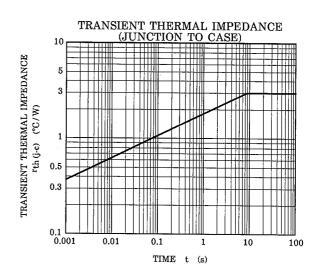












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